

10/518704
DT01 Rec'd PCT/PT 17 DEC 2004

CLAIMS OF INTERNATIONAL APPLICATION
PCT/JP2003/007857 AS AMENDED UNDER
ARTICLE 19

Express Mail No.
EV206807626US

CLAIMS

1. A thin film piezoelectric device including a substrate having a plurality of vibration spaces and a piezoelectric laminated structure formed on the substrate, a plurality of thin film piezoelectric resonators being formed facing the vibration spaces,

wherein the piezoelectric laminated structure has at least a piezoelectric film and a metal electrode formed on at least a part of each of opposite surfaces of the piezoelectric film,

the piezoelectric laminated structure comprises diaphragms positioned facing the vibration spaces, and a support area other than the diaphragms,

at least one set of two adjacent thin film piezoelectric resonators are electrically connected to each other through the metal electrode,

the thin film piezoelectric device comprising at least one set of two adjacent thin film piezoelectric resonators in which D_0 is a distance between the centers of the diaphragms of the two electrically connected adjacent thin film piezoelectric resonators and D_1 is a length of a segment of a support area on a straight line passing through centers of the diaphragms of two electrically connected adjacent thin film piezoelectric resonators, and a ratio D_1/D_0 is 0.1 to 0.5.

2. The thin film piezoelectric device according to claim 1, wherein the ratio D_1/D_0 is in a range of 0.1 to 0.5 with respect to all the sets of two electrically connected adjacent thin film piezoelectric resonators.

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3. The thin film piezoelectric device according to claim 1, wherein each of the vibration spaces is formed by a via hole extending from the surface of the substrate on which the piezoelectric laminated structure is formed to the opposite surface, and a side wall surface of the via hole forms a slant angle in a range of 80 to 100° with respect to the surface of the substrate on which the piezoelectric laminated structure is formed.

4. The thin film piezoelectric device according to claim 1, wherein the piezoelectric laminated structure comprises a lower electrode constituting the metal electrode, the piezoelectric film, and an upper electrode constituting the metal electrode stacked in order from the substrate side in at least one thin film piezoelectric resonator.

5. The thin film piezoelectric device according to claim 4, wherein the upper electrode of the at least one thin film piezoelectric resonator comprises two electrode portions.

6. The thin film piezoelectric device according to claim 1, wherein the piezoelectric laminated structure comprises a lower electrode constituting the metal electrode, a first piezoelectric film, an inner electrode constituting the metal electrode, a second piezoelectric film, and an upper electrode constituting the metal electrode stacked in order from the substrate side in at least one thin film piezoelectric resonator.

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7. The thin film piezoelectric device according to claim 1, wherein at least one insulating layer of silicon oxide and/or silicon nitride as a main component is attached to the diaphragm.

5 8. The thin film piezoelectric device according to claim 1, wherein an insulating layer comprising at least one layer of silicon oxide and/or silicon nitride as a main component intervenes only between the support area of the piezoelectric laminated structure and the substrate.

0 9. The thin film piezoelectric device according to claim 1, wherein the piezoelectric film is an oriented crystal film represented by a general formula $Al_{1-x}Ga_xN$ (where $0 < x < 1$) and consists of a solid solution of aluminum nitride and gallium nitride showing a c-axis orientation, and a rocking curve half value width (FWHM) of a diffraction peak of a (0002) surface of the film is 3.0° or less in at least one thin film piezoelectric resonator.

0 10. The thin film piezoelectric device according to claim 1, wherein the piezoelectric film is a zinc oxide thin film showing a c-axis orientation, and a rocking curve half value width (FWHM) of a diffraction peak of a (0002) surface of the film is 3.0° or less in at least one thin film piezoelectric resonator.

5 11. The thin film piezoelectric device according to claim 1, wherein the piezoelectric film is a lead titanate thin film or a lead zirconate titanate thin film in at least one thin film piezoelectric resonator.

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12. The thin film piezoelectric device according to claim 1,
wherein the planar shape of one of the diaphragms has two pairs of
opposite sides, and at least one pair of opposite sides is formed to
be non-parallel in at least one thin film piezoelectric resonator.

13. The thin film piezoelectric device according to claim 1,
wherein at least a part of the planar shape of one of the diaphragms
is formed by a non-square irregular polygonal shape in at least one
thin film piezoelectric resonator.

14. The thin film piezoelectric device according to claim 1,
wherein the planar shape of one of the diaphragms is formed by a non-
square irregular polygonal shape including a curved portion in at
least a part of the shape in at least one thin film piezoelectric
resonator.

15. The thin film piezoelectric device according to claim 1,
the thin film piezoelectric device being a thin film piezoelectric
filter.

16. The thin film piezoelectric device according to claim
15, wherein the thin film piezoelectric filter comprises a ladder type
circuit comprising a plurality of thin film piezoelectric resonators
connected in series and at least one of the thin film piezoelectric
resonators branched from/connected to the plurality of resonators
connected in series.

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17. The thin film piezoelectric device according to claim 1, the thin film piezoelectric device being a duplexer comprising a plurality of thin film piezoelectric filters.

5 18. The thin film piezoelectric device according to claim 17, wherein the thin film piezoelectric filter comprises a ladder type circuit comprising a plurality of thin film piezoelectric resonators connected in series and at least one of the thin film piezoelectric resonators branched from/connected to the plurality of resonators
0 connected in series.

19. A method of manufacturing the thin film piezoelectric device according to claim 1, comprising the steps of: forming the piezoelectric laminated structure on the substrate comprising a
5 semiconductor or an insulator; and thereafter forming the vibration spaces in the substrate from a side opposite to the side on which the piezoelectric laminated structure is fabricated by a deep graving type reactive ion etching process.

20. A thin film piezoelectric resonator formed using a substrate having a vibration space, and a piezoelectric laminated structure formed on the substrate, wherein the piezoelectric laminated structure comprises at least a piezoelectric film and a metal
electrode formed on at least a part of each of the opposite surfaces
of the piezoelectric film, the vibration space is formed by a via hole extending from the surface of the substrate on which the piezoelectric laminated structure is formed to an opposite surface, and a side wall
surface of the via hole forms an angle in a range of 80 to 100° with

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respect to the surface of the substrate on which the piezoelectric laminated structure is formed.

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